ABSTRACT OF THE DISCLOSURE

A semiconductor device according to the present invention has a configuration that a resistance section is connected to only one of a current-mirror section forming a voltage conversion circuit and an output section. With this configuration, it is possible to determine the temperature dependency of an output voltage according to S factors of transistors forming one of the current-mirror section and the output section and a resistance value of the resistance section, and to suppress manufacturing irregularities caused by irregularities of the transistors between the two sections and those among a plurality of resistance materials.